

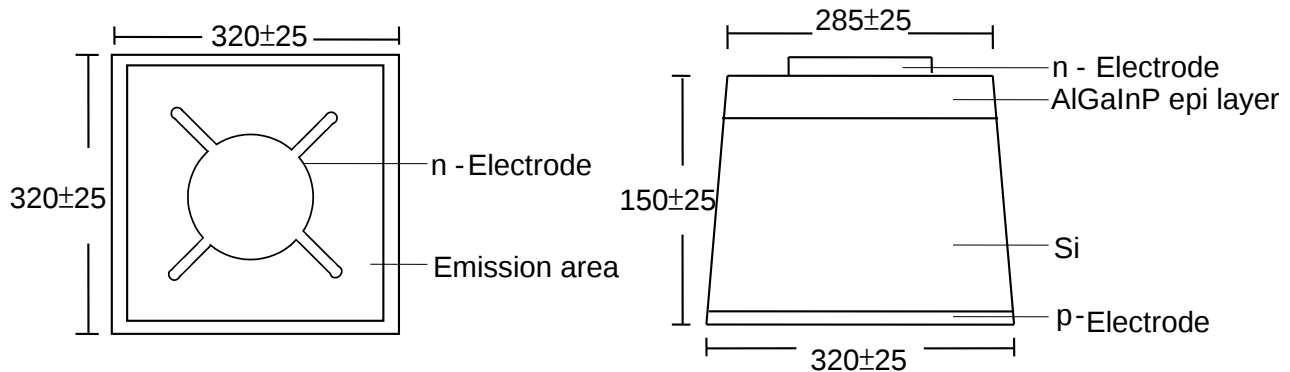
■ Features :

- Ultrabright LED chips
- Suitable for New Creative Products

■ Typical Applications :

- Special Decorations
- Plant Grow Lights

■ Outline Dimensions : (Unit: μm)



■ Physical Structure :

Chip dimension	Chip size	320±25 μm x 320±25 μm
	Thickness	150±25 μm
	Bonding pad	105±10 μm
Electrode	Top: N (cathode)	Gold
	Backside: P (anode)	Gold
Surface condition	Frosted	

*F2

■ Electro-Optical Characteristics : ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 20 \text{ mA}$	1.8	-	2.3	V
Reverse Current	I_R	$V_Z = 5 \text{ V}$	-	-	10	μA
Wavelength	λ_D	$I_F = 20 \text{ mA}$	640	-	650	nm
Spectral width at half height	$\Delta\lambda$	$I_F = 20 \text{ mA}$	-	19	-	nm
Luminous Intensity	I_v	$I_F = 20 \text{ mA}$	240		500	mcd

Fig 1. Forward Current vs. Forward Voltage

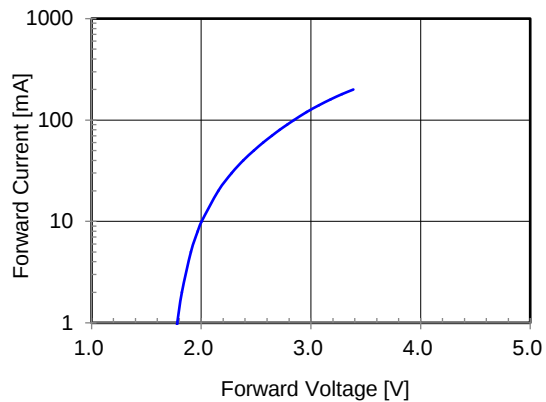


Fig 2. Relative Intensity vs. Forward Current

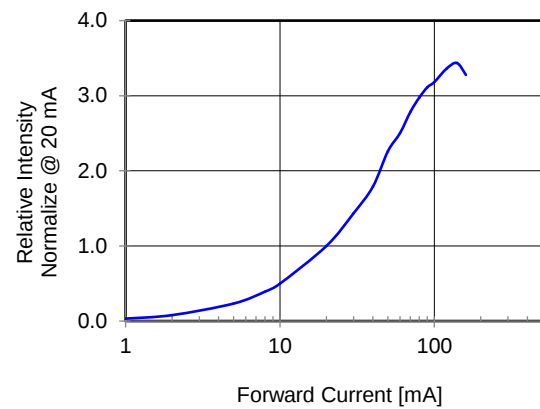


Fig 3. Forward Voltage vs. Temperature

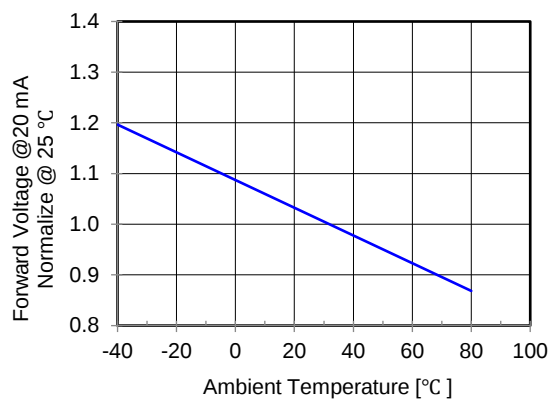


Fig 4. Relative Intensity vs. Temperature

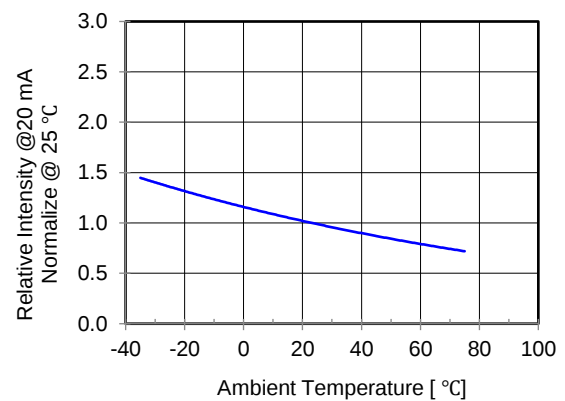


Fig 5. Relative Intensity vs. Wavelength

